

P-Channel 30 V (D-S) MOSFET



RoHS
COMPLIANT

PRODUCT SUMMARY

V _{DS} (V)	R _{DS(on)} (mΩ)(Typ.)	I _D (A)	Q _g (Typ.)
- 30	12.3at V _{GS} = - 10 V	- 45 ^d	41 nC
	17.9at V _{GS} = - 4.5 V	- 30 ^d	

FEATURES

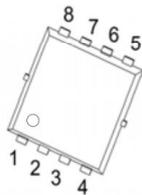
- DT-Trench Power MOSFET
- Low On-Resistance for Low Voltage Drop
- 100 % R_g and UIS Tested

APPLICATIONS

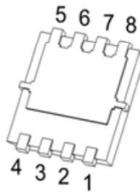
- Battery, Load and Adaptor Switches
 - Notebook Computers
 - Notebook Battery Packs

PDFN 3.3x3.3

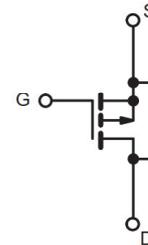
Top View



Bottom View



Top View



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C, unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	- 30	V
Gate-Source Voltage	V _{GS}	± 20	
Continuous Drain Current (T _J = 150 °C)	I _D	T _C = 25 °C	- 45 ^d
		T _C = 70 °C	- 35 ^d
		T _A = 25 °C	- 18 ^{a, b}
		T _A = 70 °C	- 9 ^{a, b}
Pulsed Drain Current (t = 100 μs)	I _{DM}	- 180	A
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C	
		T _A = 25 °C	- 3.8 ^{a, b}
Avalanche Current	I _{AS}	- 25	mJ
Single-Pulse Avalanche Energy	E _{AS}	35	
Maximum Power Dissipation	P _D	T _C = 25 °C	43
		T _C = 70 °C	26
		T _A = 25 °C	4.8 ^{a, b}
		T _A = 70 °C	3 ^{a, b}
Operating Junction and Storage Temperature Range	T _J , T _{stg}	- 55 to 150	°C
Soldering Recommendations (Peak Temperature) ^{e, f}		260	

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^{a, c}	R _{thJA}	25	30	°C/W
Maximum Junction-to-Case	R _{thJC}	2.5	3	

Notes:

a. Surface mounted on 1" x 1" FR4 board.

b. t = 10 s.

c. Maximum under steady state conditions is 70 °C/W.

d. Package limited.

e. The PDFN3.3X3.3 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.

f. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.

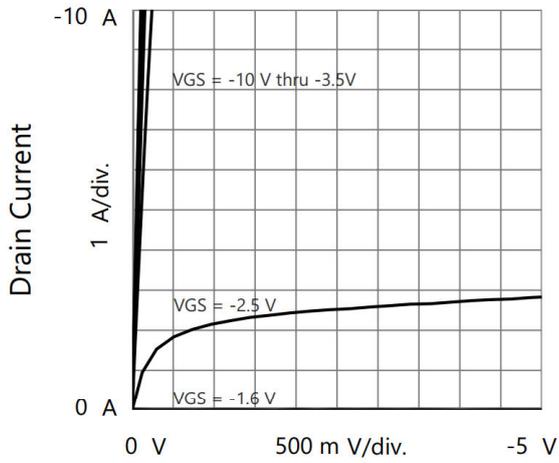
SPECIFICATIONS ($T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted)						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0, I_D = -250\text{ }\mu\text{A}$	-30			V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	$I_D = -250\text{ }\mu\text{A}$		-22		mV/ $^\circ\text{C}$
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$			4.1		
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$	-1		-3	V
Gate-Source Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -30\text{ V}, V_{GS} = 0\text{ V}$			-1	μA
		$V_{DS} = -24\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$			-5	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \geq -10\text{ V}, V_{GS} = -10\text{ V}$	-45			A
Drain-Source On-State Resistance ^a	$R_{DS(on)}$	$V_{GS} = -10\text{ V}, I_D = -15\text{ A}$		12.3	14	m Ω
		$V_{GS} = -4.5\text{ V}, I_D = -10\text{ A}$		17.9	20	
Forward Transconductance ^a	g_{fs}	$V_{DS} = -10\text{ V}, I_D = -15\text{ A}$		60		S
Dynamic^b						
Input Capacitance	C_{iss}	$V_{DS} = -15\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$		2260		pF
Output Capacitance	C_{oss}			260		
Reverse Transfer Capacitance	C_{rss}			254		
Total Gate Charge	Q_g	$V_{DS} = -15\text{ V}, V_{GS} = -10\text{ V}, I_D = -15\text{ A}$		41		nC
Gate-Source Charge	Q_{gs}			14		
Gate-Drain Charge	Q_{gd}			29		
Gate Resistance	R_g	$f = 1\text{ MHz}$		11		Ω
Turn-On Delay Time	$t_{d(on)}$	$V_{DS} = -15\text{ V}, R_L = 1.5\text{ }\Omega$ $I_D \cong -15\text{ A}, V_{GS} = -10\text{ V}, R_g = 1\text{ }\Omega$		16		ns
Rise Time	t_r			14		
Turn-Off Delay Time	$t_{d(off)}$			60		
Fall Time	t_f			12		
Turn-On Delay Time	$t_{d(on)}$	$V_{DS} = -15\text{ V}, R_L = 1.5\text{ }\Omega$ $I_D \cong -15\text{ A}, V_{GS} = -4.5\text{ V}, R_g = 1\text{ }\Omega$		60		
Rise Time	t_r			59		
Turn-Off Delay Time	$t_{d(off)}$			50		
Fall Time	t_f			22		
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	$T_C = 25\text{ }^\circ\text{C}$			-45	A
Pulse Diode Forward Current (100 μs)	I_{SM}				-180	
Body Diode Voltage	V_{SD}	$I_S = -3\text{ A}, V_{GS} = 0$		-0.7	-1.20	V
Body Diode Reverse Recovery Time	t_{rr}	$I_F = -15\text{ A}, dI/dt = 100\text{ A}/\mu\text{s}, T_J = 25\text{ }^\circ\text{C}$		22		ns
Body Diode Reverse Recovery Charge	Q_{rr}			12		nC
Reverse Recovery Fall Time	t_a			9		ns
Reverse Recovery Rise Time	t_b			13		

Notes:

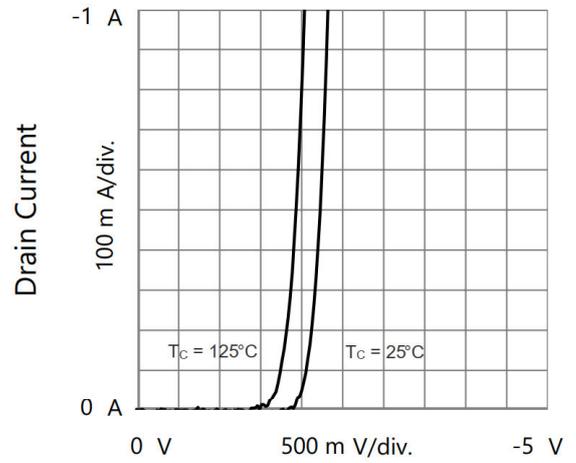
- Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
- Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

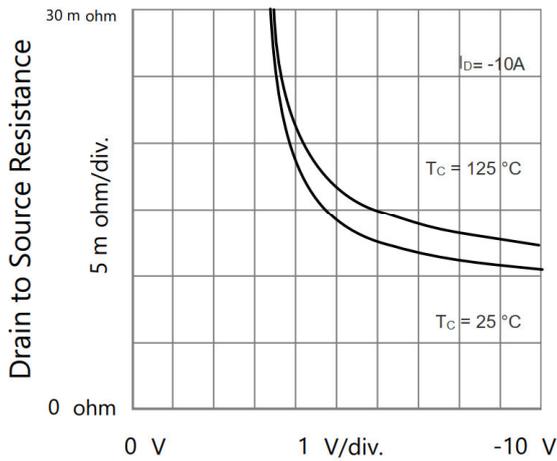
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



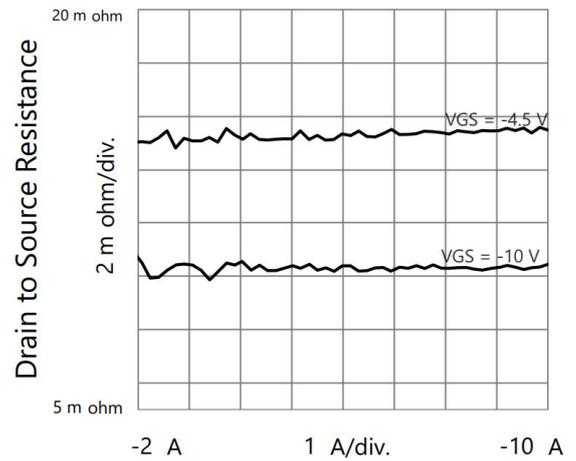
Drain to Source Voltage
Output Characteristics



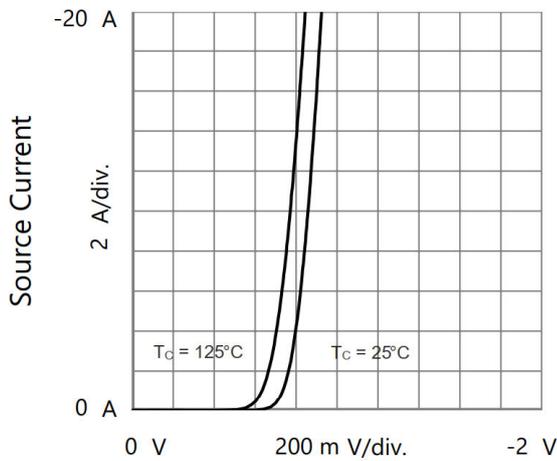
Gate to Source Voltage
Transfer Characteristics



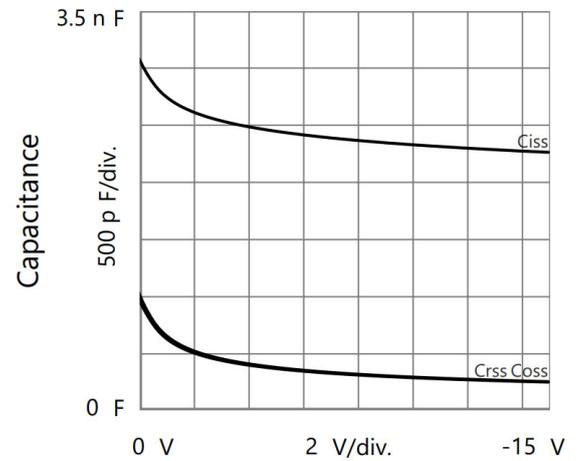
Gate to Source Voltage
Drain to Source Resistance vs. Gate to Source Voltage



Drain Current
Drain to Source Resistance vs. Drain Current

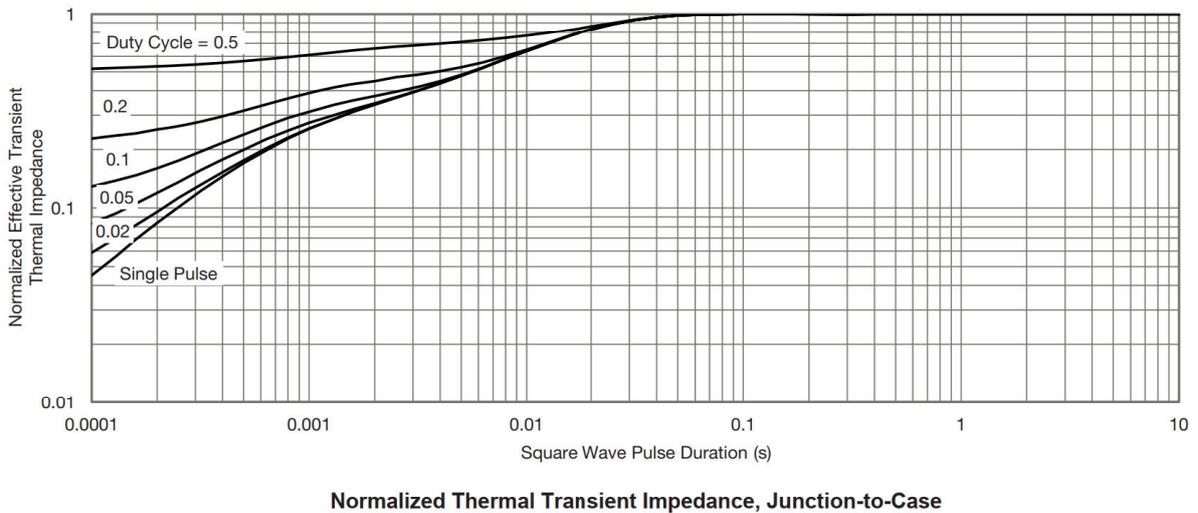
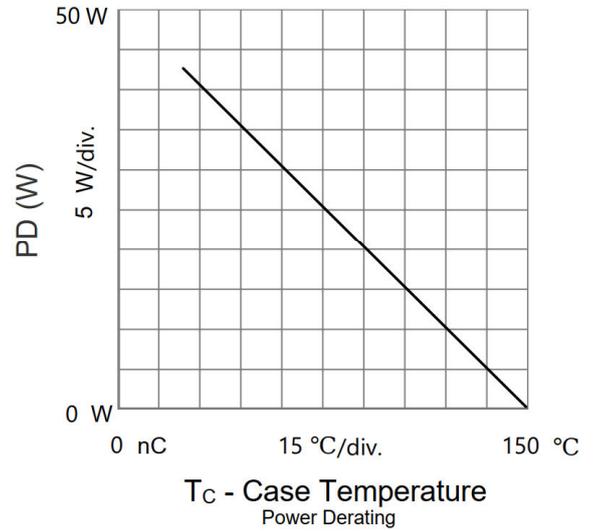
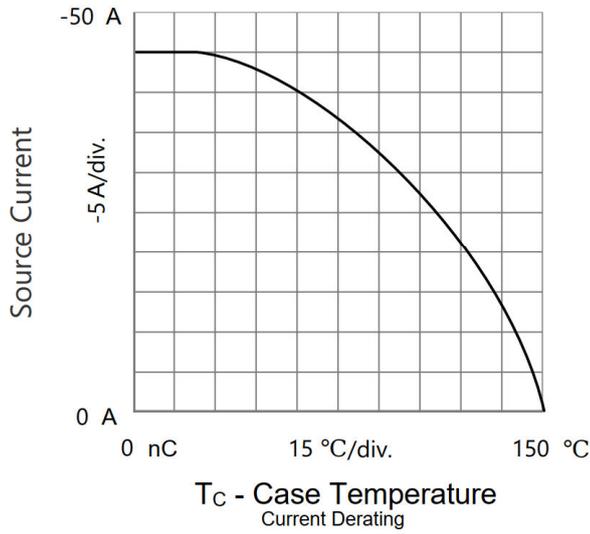
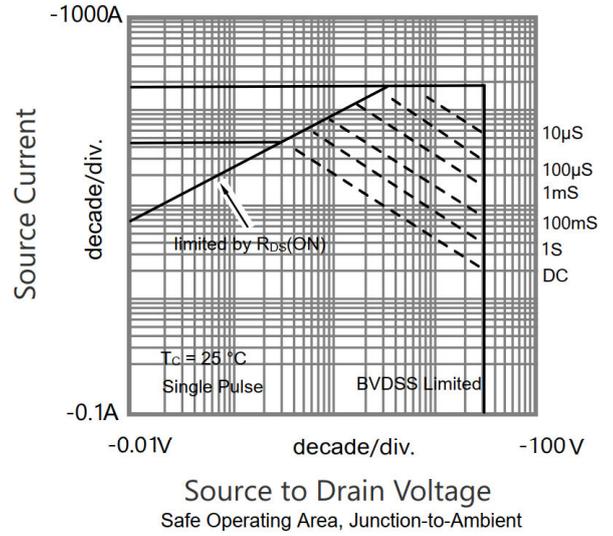
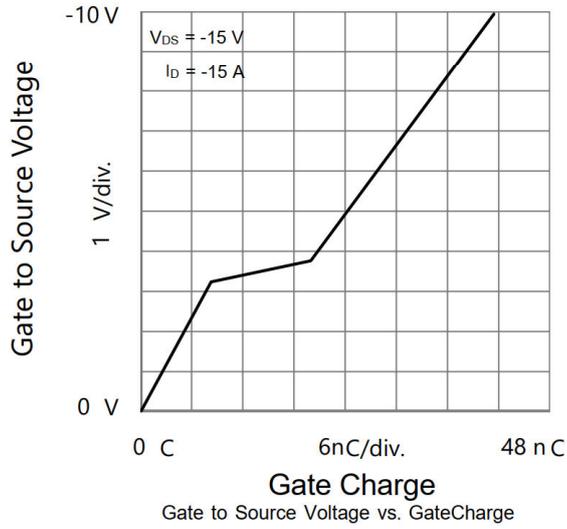


Source to Drain Voltage
Body Diode Forward Characteristics



Drain to Source Voltage
Capacitances

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



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